Single 2-Input NAND Gate

NLV74HC1G00

The NLV74HC1G00 is a high speed CMOS 2−input NAND gate fabricated silicon gate CMOS technology.

The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output.

The NLV74HC1G00 output drive current is 1/2 compared to MC74HC series.

Features

- High Speed: t_{PD} = 7 ns (Typ) at V_{CC} = 5 V
- Low Power Dissipation: I_{CC} = 1 μA (Max) at T_A = 25°C
- High Noise Immunity
- Balanced Propagation Delays ($t_{pLH} = t_{pHL}$)
- Symmetrical Output Impedance ($I_{OH} = I_{OL}$ = 2 mA)
- Chip Complexity: < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

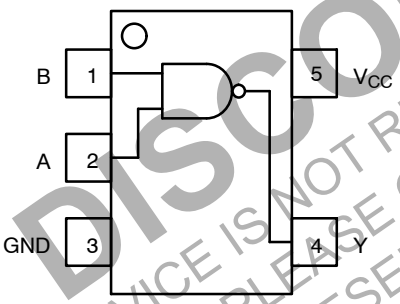


Figure 1. Pinout

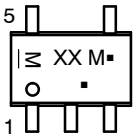
Figure 2. Logic Symbol

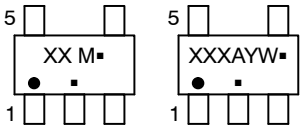
PIN ASSIGNMENT	
1	B
2	A
3	GND
4	Y
5	V_{CC}

SC−88A
DF SUFFIX
CASE 419A

TSOP−5
DT SUFFIX
CASE 483

MARKING DIAGRAMS





Commercial **NLV Prefix**

XXX = Device Code
M = Date Code*
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

FUNCTION TABLE

Inputs		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 6 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_{IN}	DC Input Voltage		−0.5 to V_{CC} +0.5	V
V_{OUT}	DC Output Voltage		−0.5 to V_{CC} +0.5	V
I_{IK}	DC Input Diode Current		±20	mA
I_{OK}	DC Output Diode Current		±20	mA
I_{OUT}	DC Output Source/Sink Current		±12.5	mA
I_{CC} or I_{GND}	DC Supply Current per Supply Pin or Ground Pin		±25	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 1)	SC−88A TSOP−5	377 320	°C/W
P_D	Power Dissipation in Still Air at 85°C	SC−88A TSOP−5	332 390	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage (Note 2)	Human Body Model Charged Device Model	2000 1000	V
$I_{LATCHUP}$	Latchup Performance (Note 3)		±500	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 20 ounce copper trace with no air flow per JESD51−7.
2. HBM tested to ANSI/ESDA/JEDEC JS−001−2017. CDM tested to JESD22−C101−F. JEDEC recommends that ESD qualification to EIA/JESD22−A115A (Machine Model) be discontinued per JEDEC/JEP172A.
3. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage	2.0	6.0	V
V_{IN}	DC Input Voltage	0.0	V_{CC}	V
V_{OUT}	DC Output Voltage	0.0	V_{CC}	V
T_A	Operating Temperature Range	−55	+125	°C
t_r , t_f	Input Rise and Fall Time V_{CC} = 2.0 V V_{CC} = 3.0 V V_{CC} = 4.5 V V_{CC} = 6.0 V	 0 0 0 0	 1000 600 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

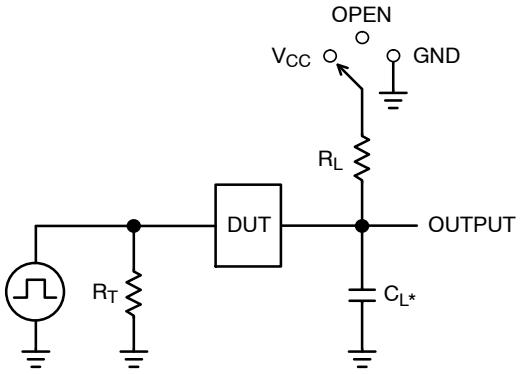
Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = 25°C Min	T_A = 25°C Typ	T_A = 25°C Max	−40°C ≤ T_A ≤ 85°C Min	−40°C ≤ T_A ≤ 85°C Max	−55°C ≤ T_A ≤ 125°C Min	−55°C ≤ T_A ≤ 125°C Max	Unit
V_{IH}	High−Level Input Voltage		2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.20	– – – –	– – – –	1.5 2.1 3.15 4.20	– – – –	1.5 2.1 3.15 4.20	– – – –	V
V_{IL}	Low−Level Input Voltage		2.0 3.0 4.5 6.0	– – – –	– – – –	0.5 0.9 1.35 1.80	– – – –	0.5 0.9 1.35 1.80	– – – –	0.5 0.9 1.35 1.80	V
V_{OH}	High−Level Output Voltage	V_{IN} = V_{IH} or V_{IL} I_{OH} = −20 μA	2.0 3.0 4.5 6.0	1.9 2.9 4.4 5.9	2.0 3.0 4.5 6.0	– – – –	1.9 2.9 4.4 5.9	– – – –	1.9 2.9 4.4 5.9	– – – –	V
		V_{IN} = V_{IH} or V_{IL} I_{OH} = −2 mA I_{OH} = −2.6 mA	4.5 6.0	4.18 5.68	4.31 5.80	– –	4.13 5.63	– –	4.08 5.58	– –	
V_{OL}	Low−Level Output Voltage	V_{IN} = V_{IH} or V_{IL} I_{OL} = 20 μA	2.0 3.0 4.5 6.0	– – – –	0.0 0.0 0.0 0.0	0.1 0.1 0.1 0.1	– – – –	0.1 0.1 0.1 0.1	– – – –	0.1 0.1 0.1 0.1	V
		V_{IN} = V_{IH} or V_{IL} I_{OL} = 2 mA I_{OL} = 2.6 mA	4.5 6.0	– –	0.17 0.18	0.26 0.26	– – –	0.33 0.33	– –	0.40 0.40	
I_{IN}	Input Leakage Current	V_{IN} = 6.0 V or GND	6.0	–	–	±0.1	–	±1.0	–	±1.0	μA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND	6.0	–	–	1.0	–	10	–	40	μA

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	T_A = 25°C			−40°C ≤ T_A ≤ 85°C		−55°C ≤ T_A ≤ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay, (A or B) to Y	V_{CC} = 5.0 V C_L = 15 pF	–	3.5	15	–	20	–	25	ns
		V_{CC} = 2.0 V C_L = 50 pF	–	20	100	–	125	–	155	
		V_{CC} = 3.0 V	–	11	27	–	35	–	90	
		V_{CC} = 4.5 V	–	8	20	–	25	–	35	
		V_{CC} = 6.0 V	–	7	17	–	21	–	26	
t_{TLH}, t_{THL}	Output Transition Time	V_{CC} = 5.0 V C_L = 15 pF	–	3	10	–	15	–	20	ns
		V_{CC} = 2.0 V C_L = 50 pF	–	25	125	–	155	–	200	
		V_{CC} = 3.0 V	–	16	35	–	45	–	60	
		V_{CC} = 4.5 V	–	11	25	–	31	–	38	
		V_{CC} = 6.0 V	–	9	21	–	26	–	32	
C_{IN}	Input Capacitance		–	5	10	–	10	–	10	pF

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 4)	10	pF

4. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



Test	Switch Position	C_L, pF	R_L, Ω
t_{PLH} / t_{PHL}	Open	See AC Characteristics Table	X
t_{TLH} / t_{THL} (Note 5)	Open		X
t_{PLZ} / t_{PZL}	V_{CC}		1 k
t_{PHZ} / t_{PZH}	GND		1 k

X – Don't Care

*C_L includes probe and jig capacitance
R_T is Z_{OUT} of pulse generator (typically 50 W)
f = 1 MHz

Figure 3. Test Circuit

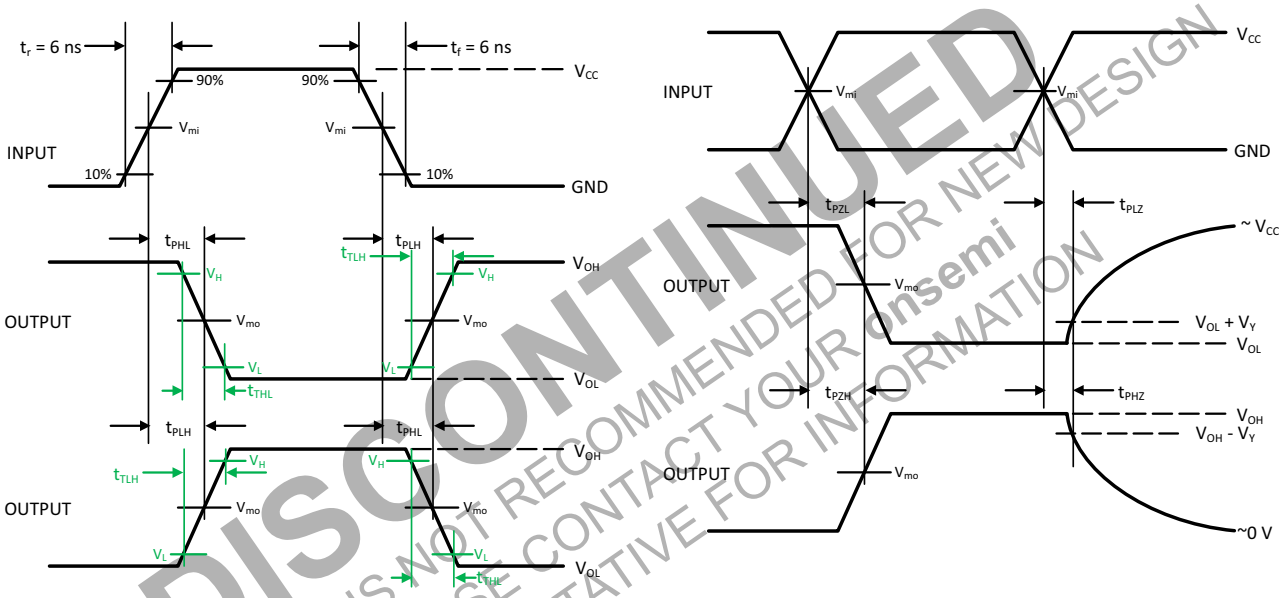


Figure 4. Switching Waveforms

V_{CC}, V	V_{mi}, V	V_{mo}, V		V_L, V	V_H, V	V_Y, V
		t_{PLH}, t_{PHL}	t_{PZL}, t_{PLZ}, t_{PZH}, t_{PHZ}			
3.0 to 3.6	V_{CC}/2	V_{CC}/2	V_{CC}/2	V_{OL} + 0.1 (V_{OH} – V_{OL})	V_{OL} + 0.9 (V_{OH} – V_{OL})	0.3
4.5 to 5.5	V_{CC}/2	V_{CC}/2	V_{CC}/2	V_{OL} + 0.1 (V_{OH} – V_{OL})	V_{OL} + 0.9 (V_{OH} – V_{OL})	0.3

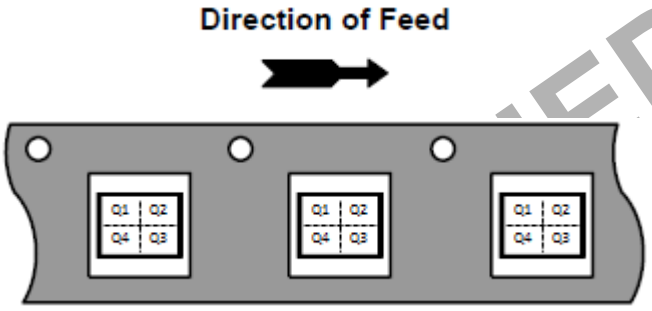
5. t_{TLH} and t_{THL} are measured from 10% to 90% of (V_{OH} – V_{OL}), and 90% to 10% of (V_{OH} – V_{OL}), respectively.

ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping†
NLV74HC1G00DFT1G*	SC−88A	H1	Q2	3000 / Tape & Reel
MC74HC1G00DFT2G−L22038	SC−88A	H1	Q4	3000 / Tape & Reel
NLVHC1G00DFT2G*	SC−88A	H1	Q4	3000 / Tape & Reel
MC74HC1G00DTT1G	TSOP−5	H1	Q4	3000 / Tape & Reel
NLV74HC1G00DTT1G*	TSOP−5	H1	Q4	3000 / Tape & Reel

†For complete information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

PIN 1 ORIENTATION IN TAPE AND REEL

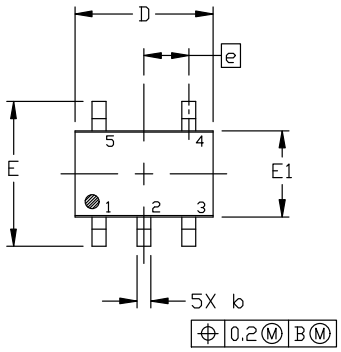


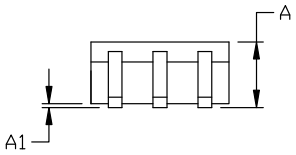
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

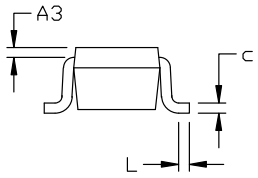
SCALE 2:1

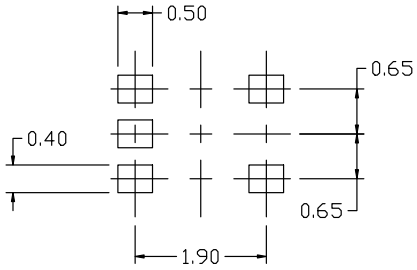
SC−88A (SC−70−5/SOT−353)
CASE 419A−02
ISSUE M

DATE 11 APR 2023









RECOMMENDED
MOUNTING FOOTPRINT

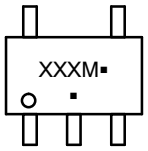
* For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.80	0.95	1.10
A1	---	---	0.10
A3	0.20 REF		
b	0.10	0.20	0.30
c	0.10	---	0.25
D	1.80	2.00	2.20
E	2.00	2.10	2.20
E1	1.15	1.25	1.35
e	0.65 BSC		
L	0.10	0.15	0.30

GENERIC MARKING DIAGRAM*



*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

STYLE 1:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

STYLE 3:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. CATHODE 1

STYLE 4:
PIN 1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2

STYLE 5:
PIN 1. CATHODE
2. COMMON ANODE
3. CATHODE 2
4. CATHODE 3
5. CATHODE 4

STYLE 6:
PIN 1. EMITTER 2
2. BASE 2
3. EMITTER 1
4. COLLECTOR
5. COLLECTOR 2/BASE 1

STYLE 7:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

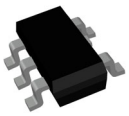
STYLE 8:
PIN 1. CATHODE
2. COLLECTOR
3. N/C
4. BASE
5. EMITTER

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. ANODE
5. ANODE

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

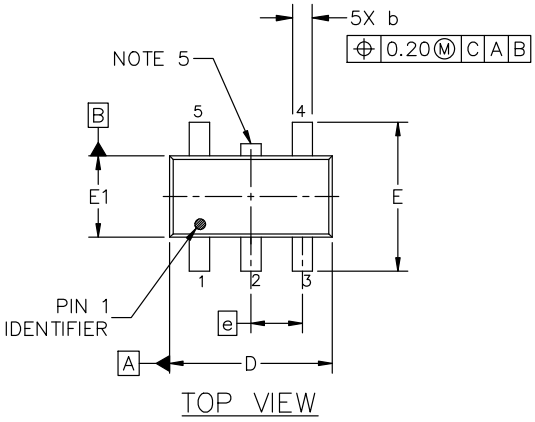
DOCUMENT NUMBER:	98ASB42984B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	SC−88A (SC−70−5/SOT−353)	PAGE 1 OF 1

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

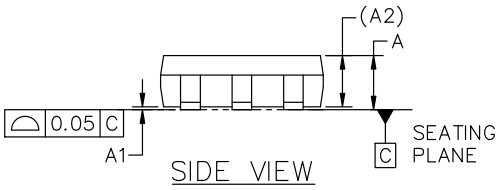


TSOP−5 3.00x1.50x0.95, 0.95P
CASE 483
ISSUE P

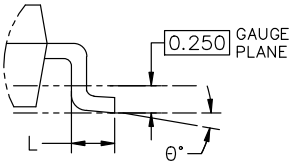
DATE 01 APR 2024



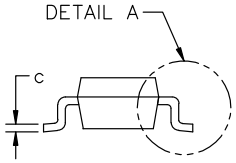
TOP VIEW



SIDE VIEW



DETAIL "A"
SCALE 2:1

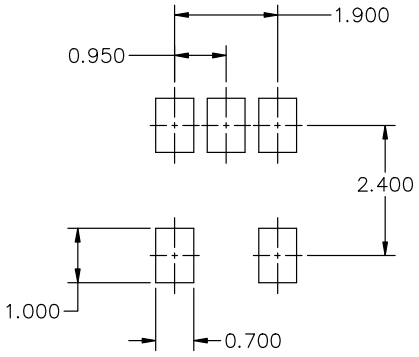


END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS (ANGLES IN DEGREES).
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION D.
5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

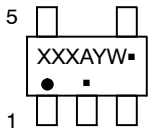
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.900	1.000	1.100
A1	0.010	0.055	0.100
A2		0.950 REF.	
b	0.250	0.375	0.500
c	0.100	0.180	0.260
D	2.850	3.000	3.150
E	2.500	2.750	3.000
E1	1.350	1.500	1.650
e		0.950 BSC	
L	0.200	0.400	0.600
θ	0°	5°	10°



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

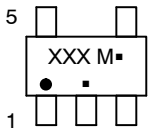
GENERIC
MARKING DIAGRAM*



Analog

XXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)



Discrete/Logic

XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	**98ARB18753C**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**TSOP−5 3.00x1.50x0.95, 0.95P**	**PAGE 1 OF 1**

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